



Enhanced emission of $Tm^{3+} : ^3F_4 \rightarrow ^3H_6$ transition by backward energy transfer from Yb^{3+} in Y_2O_3 for mid-infrared applications

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ABSTRACT

Tm^{3+} doped luminescence materials have attracted great attention owing to their potential for achieving 2 μm laser. Here, we report that the 2 μm emission intensity of $Tm^{3+} : ^3F_4 \rightarrow ^3H_6$ transition can be enhanced by as large as 1.8 times through introducing Yb^{3+} into Tm^{3+} doped Y_2O_3 upon 782 nm excitation, where the population of $Tm^{3+} : ^3F_4$ level is increased by backward energy transfer from Yb^{3+} following the forward energy transfer from the upper level $Tm^{3+} : ^3H_4$ to an intermediate level $Yb^{3+} : ^2F_{5/2}$. In addition, the efficiencies of Yb^{3+} to Tm^{3+} backward energy transfer are determined based on the analysis of emission spectra and fluorescence time profiles. It is found that the Yb^{3+} to Tm^{3+} backward energy transfer upon Tm^{3+} excitation at 782 nm is more efficient than the Yb^{3+} to Tm^{3+} energy transfer upon Yb^{3+} direct excitation at 980 nm, which is explained by the preferential excitation of Yb^{3+} with a nearby Tm^{3+} in the forward energy transfer from Tm^{3+} to Yb^{3+} upon Tm^{3+} excitation. Our results demonstrate that codoping Yb^{3+} into Tm^{3+} activated materials offers a promising approach to obtain efficient 2 μm laser, and the efficient backward energy transfer may play a key role in other rare earth ions doped luminescence materials.

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1. Introduction

Recently, great attention has been paid to the infrared lasers. Particularly, 2 μm lasers have received intense research for their potential applications including medicine, remote sensing and military technologies [1–7]. Among various rare earth (RE) ions who possess abundant levels, Ho^{3+} and Tm^{3+} are the most probable activators to generate 2 μm laser due to the transitions of $Ho^{3+} : ^5I_7 \rightarrow ^5I_8$ and $Tm^{3+} : ^3F_4 \rightarrow ^3H_6$ emissions [8–12]. The laser operation of Ho^{3+} is limited because there is no available upper level in Ho^{3+} to be excited from the ground level with the commercial 800 or 980 nm laser diodes. Therefore, the desirable 2 μm emission of Ho^{3+} can be obtained only when the sensitizer Yb^{3+} is codoped to provide efficient absorption at 980 nm [13–16]. As for Tm^{3+} , it has a reasonable absorption around 800 nm to be directly pumped by the available laser diodes and the broad emission about 300 nm allowing wide wavelength tuning [17,18].

For mid-infrared laser, an ideal host should possess low phonon energy to reduce multiphonon relaxation and thus increase the quantum efficiency. However, since resonant pumping cannot provide full population inversion and good signal-to-noise ratio, an upper level instead of the emitting level is pumped; therefore, populating the emitting level from the upper level becomes difficult owing to the slow multiphonon relaxation and the small branching ratio [19–21]. Accordingly, several RE ions such as Pr^{3+} , Eu^{3+} and Ce^{3+} , have been used as the codopants to regulate the population [22–25]. For example, codoping Ce^{3+} into Er^{3+} activated luminescence augments the population of the $^4I_{13/2}$ level at the expense of that of the $^4I_{11/2}$ level due to the energy transfer from $Er^{3+} (^4I_{11/2} - ^4I_{13/2})$ to $Ce^{3+} (^2F_{5/2} - ^2F_{7/2})$, resulting in an enhancement of the 1550 nm emission to realize laser operation pumped by 980 nm [26,27]. The incorporation of Ce^{3+} can also enhance the emission of $Ho^{3+} : ^5I_7 \rightarrow ^5I_8$ to obtain 2 μm laser [28,29]. Besides, Özen et al. [30–32] studied the blue upconversion emission of Tm^{3+} under red light excitation at 683 nm in Tm^{3+} and Yb^{3+} codoped fluorophosphate glasses. They observed a considerable enhancement of the blue upconversion emission in the presence of

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Yb^{3+} due to the increased population of $^3\text{F}_4$ from which the blue level $^1\text{G}_4$ is reached by absorbing a red photon.

The sesquioxide Y_2O_3 is a suitable matrix for RE^{3+} activated solid state lasers because of their excellent properties like good chemical stability, low thermal expansion and high thermal conductivity [33–35]. Moreover, it can be made into highly transparent ceramic with large sizes as well as good transparency even in the infrared region, which has been applied to obtain high power solid state lasers [36–38]. In addition, Y_2O_3 possesses relatively low phonon energy (phonon cutoff $\approx 591 \text{ cm}^{-1}$) [39], which is beneficial to the $2 \mu\text{m}$ emission of $\text{Tm}^{3+}:\text{F}_4 \rightarrow ^3\text{H}_6$ but also results in a relative low feeding to $^3\text{F}_4$ level upon 782 nm excitation. Generally, the population of $^3\text{F}_4$ level can be doubled due to the cross relaxation energy transfer ($^3\text{H}_4, ^3\text{H}_6 \rightarrow ^3\text{F}_4, ^3\text{F}_4$) when the Tm^{3+} concentration is high enough [17].

In the present work, we introduce Yb^{3+} into Tm^{3+} doped Y_2O_3 to enhance the $2 \mu\text{m}$ emission intensity of $\text{Tm}^{3+}:\text{F}_4 \rightarrow ^3\text{H}_6$ transition upon 782 nm excitation, in which the population of $^3\text{F}_4$ level is increased by the effect of $\text{Tm}^{3+}-\text{Yb}^{3+}-\text{Tm}^{3+}$ forward-backward energy transfer (FBET), i.e. the forward energy transfer (FET) from the upper level $\text{Tm}^{3+}:\text{H}_4$ to an intermediate level $\text{Yb}^{3+}:\text{F}_{5/2}$ and the subsequent backward energy transfer (BET) from Yb^{3+} to Tm^{3+} for populating the lower level of $\text{Tm}^{3+}:\text{F}_4$. Furthermore, the BET efficiencies from Yb^{3+} to Tm^{3+} in the FBET process are calculated based on the analysis of emission spectra and fluorescence time profiles. The results are also compared with the energy transfer efficiencies upon Yb^{3+} direct excitation at 980 nm, indicating that the Yb^{3+} to Tm^{3+} backward energy transfer in FBET is more efficient than the Yb^{3+} to Tm^{3+} energy transfer upon Yb^{3+} direct excitation at 980 nm. A preferential excitation of Yb^{3+} with a nearby Tm^{3+} in the FET process is proposed to explain the efficient Yb^{3+} to Tm^{3+} backward energy transfer.

2. Experimental

2.1. Sample preparation

The samples series of $(\text{Y}_{(1-x-y)}\text{Tm}_y\text{Yb}_x)_2\text{O}_3$ ($x = 0-0.1$, $y = 0.0005-0.01$) powders were synthesized via the normal firing precursor method, which is considered to be more favorable to obtain uniform and highly crystallized samples than the traditional solid-state reaction. Typically, the appropriate amounts of Y_2O_3 (5N), Tm_2O_3 (5N) and Yb_2O_3 (6N) were first dissolved in dilute nitric acid (G.R.), respectively, to get the $\text{Y}(\text{NO}_3)_3$, $\text{Tm}(\text{NO}_3)_3$ and $\text{Yb}(\text{NO}_3)_3$ solutions. $\text{Tm}(\text{NO}_3)_3$, $\text{Yb}(\text{NO}_3)_3$ and $\text{Y}(\text{NO}_3)_3$ solutions were mixed stoichiometrically and stirred vigorously for 30 min at room temperature, and then dried at 95°C for 24 h in a drying oven, followed by being preheated at 700°C for 3 h to obtain the precursor. After grinding, the precursor was put into an alumina crucible and sintered at 1600°C for 5 h in air.

2.2. Measurements and characterization

The crystal structure of samples were characterized by X-ray diffraction (XRD) (Bruker D8 Focus diffractometer with $\text{Cu K}\alpha$ radiation $\lambda = 1.54056 \text{ \AA}$). The emission spectra were measured using FLS920 spectrometer (Edinburgh Instruments, U.K.) in the wavelength range from 900 to 1700 nm. A 782 nm and a 980 nm laser diodes were used to pump $\text{Tm}^{3+}:\text{H}_4$ level and $\text{Yb}^{3+}:\text{F}_{5/2}$ level, respectively. The output excitation power density of 782 nm laser diodes was fixed at 35 mW/mm^2 while that of 980 nm laser diodes was fixed at 5 mW/mm^2 . In fluorescence lifetime measurements, an optical parametric oscillator (OPO) was used as an excitation source and the signal was detected by a Tektronix digital oscilloscope (TDS 3052). All the measurements were carried out at room

temperature.

3. Results and discussion

As shown in Fig. 1, the XRD patterns of Tm^{3+} and/or Yb^{3+} doped Y_2O_3 matches well with the JCPDS standard patterns of Y_2O_3 (PDF #41-1105), respectively. No impurity phase can be detected, indicating the formation of pure phase.

Fig. 2a and b show the emission spectra of $(\text{Y}_{0.999-x}\text{Tm}_{0.0005}\text{Yb}_x)_2\text{O}_3$ with a fixed Tm^{3+} concentration at 0.05 mol\% and various Yb^{3+} concentrations x from 0 to 0.1 upon $\text{Tm}^{3+}:\text{H}_4$ excitation at 782 nm, respectively. In Fig. 2b, the emission intensity of $\text{Tm}^{3+}:\text{F}_4 \rightarrow ^3\text{H}_6$ transition in Tm^{3+} singly doped sample is scaled to that in codoped sample. The emission spectra of the codoped samples consist of three emission bands around 900–1200 nm, 1350–1580 nm and 1580–1700 nm, which are assigned to $\text{Yb}^{3+}:\text{F}_{5/2} \rightarrow ^2\text{F}_{7/2}$ transition, $\text{Tm}^{3+}:\text{H}_4 \rightarrow ^3\text{F}_4$ and $^3\text{F}_4 \rightarrow ^3\text{H}_6$ transitions, respectively. It should be noted that the peak around 1630 nm is only a part of $\text{Tm}^{3+}:\text{F}_4 \rightarrow ^3\text{H}_6$ emission (the complete emission is in the range of 1600–2200 nm) because the InGaAs detector used has a cutoff wavelength of 1650 nm. The appearance of Yb^{3+} emission in the codoped samples indicates the existence of energy transfer from $\text{Tm}^{3+}:\text{H}_4$ level to $\text{Yb}^{3+}:\text{F}_{5/2}$ level. It is clear that the absolute intensity of $\text{Tm}^{3+}:\text{F}_4 \rightarrow ^3\text{H}_6$ emission in the codoped sample has a remarkable enhancement with increasing x when compared with the Tm^{3+} singly doped sample, and it increases by as high as 1.8 times at $x = 0.1$ (see Fig. 2a). This enhancement directly reflects the effect of the FBET processes, as shown in Fig. 3, which has been reported in $\text{Er}^{3+}-\text{Yb}^{3+}$ system as well [40]. To evaluate the efficiency of FBET, the efficiencies of both FET and BET should be known first.

The energy transfer efficiency can be calculated by

$$\eta = 1 - \frac{\tau}{\tau_0} \quad (1)$$

where τ_0 and τ denote the excited state lifetimes of donor in the absence and in the presence of acceptor, respectively. To obtain $\text{Tm}^{3+}:\text{H}_4$ lifetimes, the fluorescence decay curves of $\text{Tm}^{3+}:\text{H}_4$ level are measured by monitoring the $\text{Tm}^{3+}:\text{H}_4 \rightarrow ^3\text{H}_6$ emission at

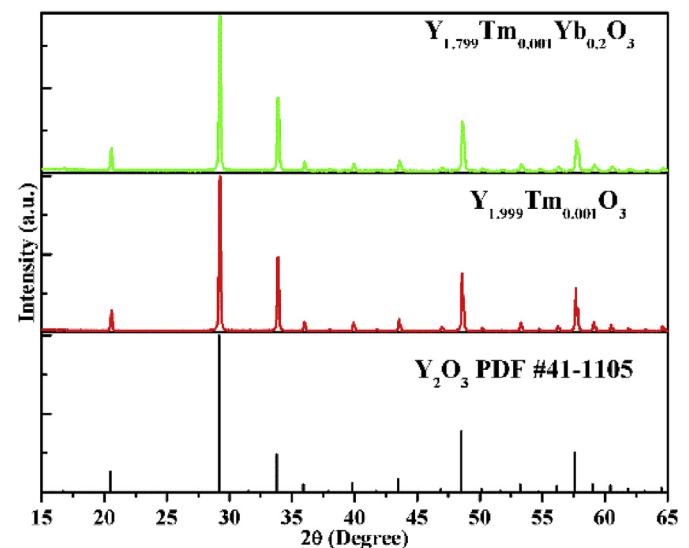


Fig. 1. The XRD patterns of Tm^{3+} and/or Yb^{3+} doped Y_2O_3 , the standard pattern of Y_2O_3 (PDF #41-1105) is also presented for comparison.

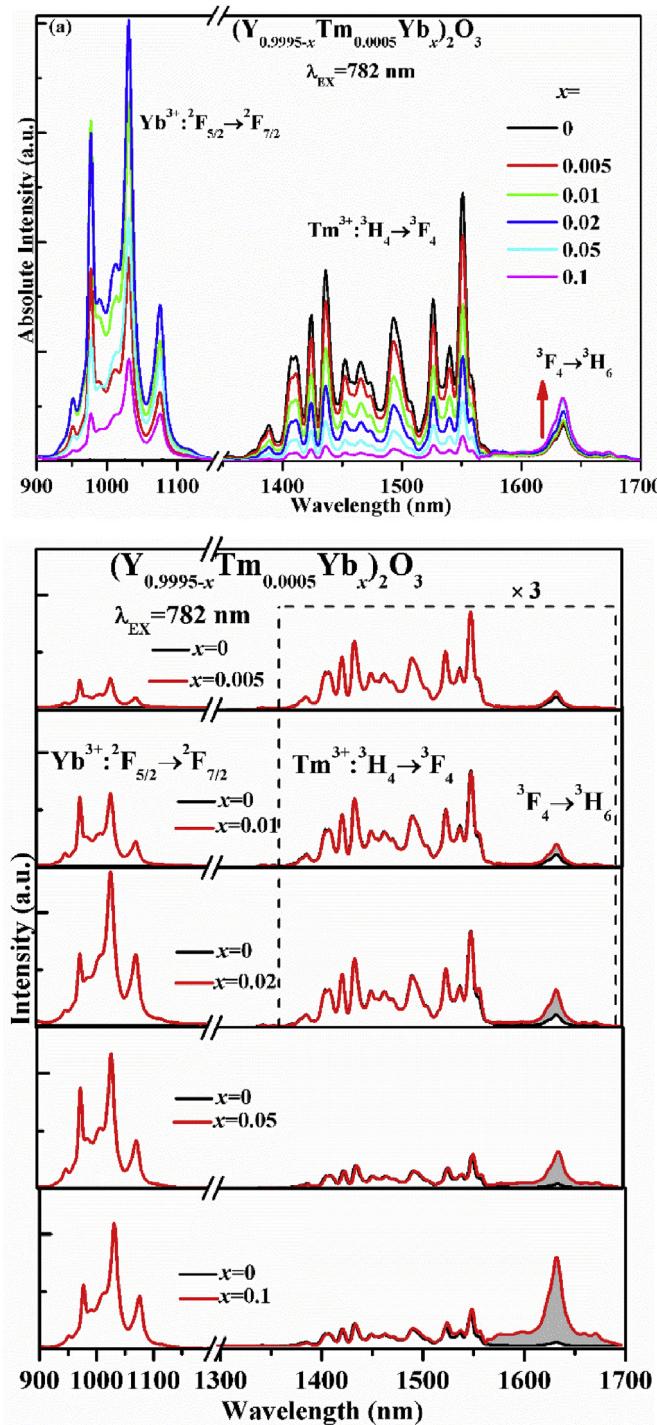


Fig. 2. a and b Emission spectra of $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) upon excitation to $Tm^{3+}:^3H_4$ level at 782 nm. The intensity of $^3H_4 \rightarrow ^3F_4$ emission in each spectrum is normalized in Fig. 2b.

811 nm under the excitation of $Tm^{3+}:^3F_3$ at 683 nm, as shown in Fig. 4. Using Eq. (1), the efficiencies of FET from Tm^{3+} to Yb^{3+} η_{Tm-Yb} are calculated and listed in Table 1. It is exhibited that η_{Tm-Yb} reaches 88% in Y_2O_3 for codoping with 10 mol% Yb^{3+} . In order to obtain the efficiency of BET from Yb^{3+} to Tm^{3+} , η_{Yb-Tm} , it is necessary to study the dynamical processes for populating $Tm^{3+}:^3F_4$ level in the absence and in the presence of FBET. In the absence of FBET, for Tm^{3+} singly doped sample, the $Tm^{3+}:^3F_4$ level is populated by 3H_4

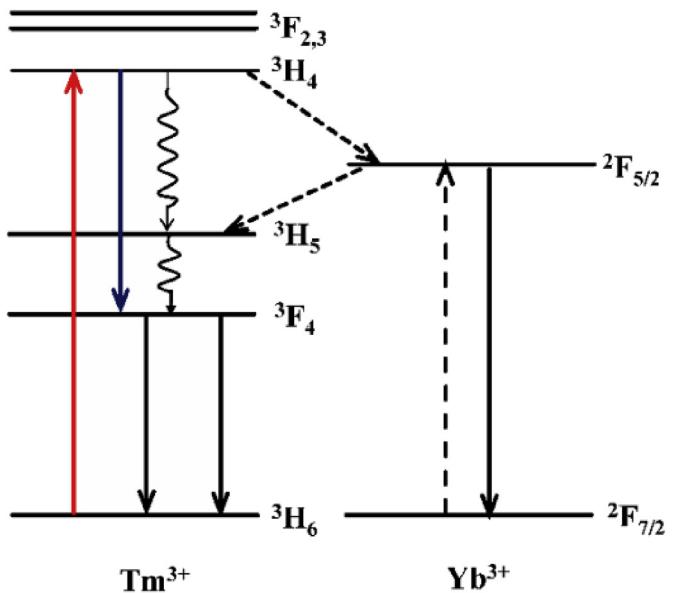


Fig. 3. Energy level diagrams and FBET process in Tm^{3+} and Yb^{3+} codoped crystal upon excitation to $Tm^{3+}:^3H_4$ level at 782 nm.

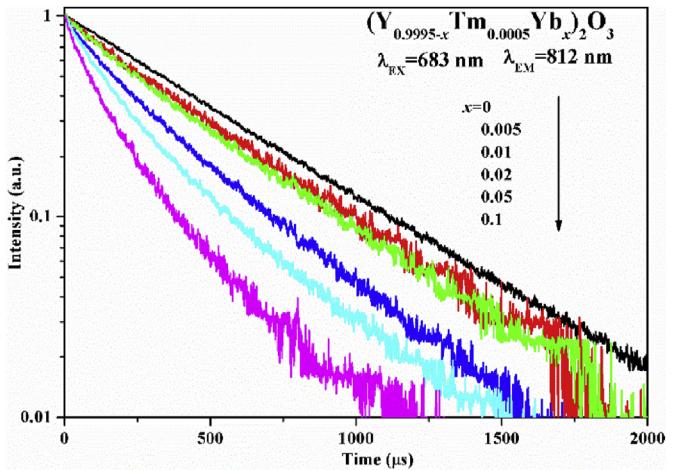


Fig. 4. Fluorescent decay curves of $Tm^{3+}:^3H_4$ level in $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) upon excitation to $Tm^{3+}:^3F_3$ level at 683 nm.

Table 1

The lifetimes of $Tm^{3+}:^3H_4$ level, and the efficiencies of FET, FET, BET and FBET in $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$).

x	$Tm^{3+}:^3H_4$ (μs)	η_{Tm-Yb}	η_{Yb-Tm}	η_{FBET}
	$\lambda_{EX} = 683$ nm			
	$\lambda_{EM} = 812$ nm			
0	458			
0.005	397.7	0.13	0.82	0.11
0.01	343.3	0.25	0.74	0.19
0.02	359.5	0.43	0.79	0.34
0.05	126.7	0.72	0.90	0.65
0.1	57	0.88	0.88	0.77

level via intrinsic relaxation including multi-phonon relaxation (MPR) via 3H_5 level and the radiative transitions to 3H_5 or directly to 3F_4 levels. In other words, except the radiative transition to the ground state, all the rest of the population of 3H_4 level feeds the 3F_4

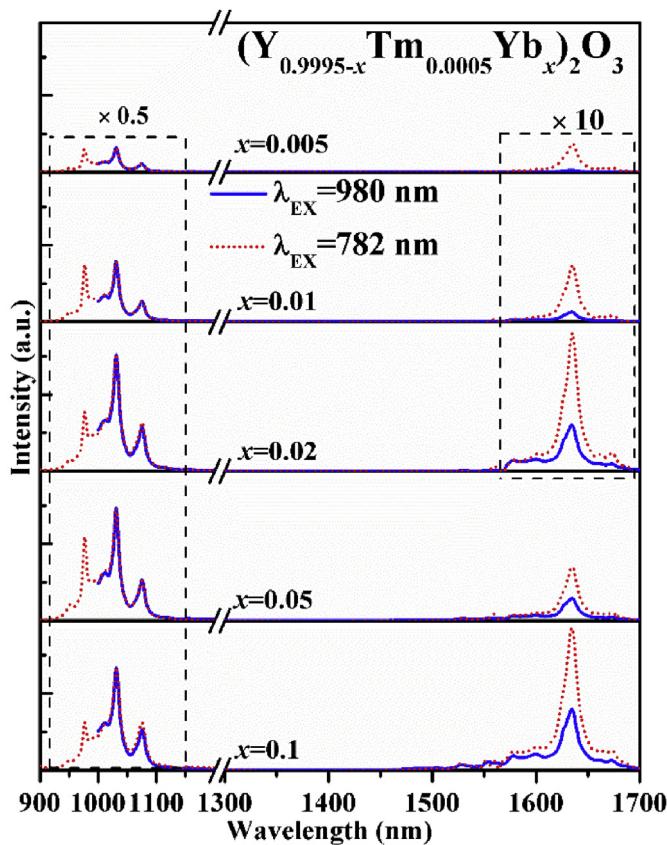


Fig. 5. Emission spectra of $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) upon 980 nm direct excitation to $Yb^{3+}\text{:}^2F_{5/2}$ level (solid). For comparison, the corresponding emission spectra upon excitation to $Tm^{3+}\text{:}^3H_4$ level at 782 nm (dotted) are also given. Note that the intensity of Yb^{3+} emission upon 980 nm excitation is scaled to that upon 782 nm excitation.

level in the Tm^{3+} singly doped sample. Note the cross relaxation (CR) process between two Tm^{3+} ions, described as $(^3H_4, ^3H_6) \rightarrow (^3F_4, ^3F_4)$ [17], is neglected for populating the 3F_4 level since Tm^{3+} concentration is fixed at as low as 0.05 mol% in this work. θ is defined as the ratio of the rate of intrinsic relaxation of $^3H_4 \rightarrow ^3F_4$ to the total rate of intrinsic decay of 3H_4 in Tm^{3+} singly doped sample and thus it is reasonable to suppose θ is independent of Yb^{3+} concentration. In the presence of FBET for the codoped samples, the origin of $Tm^{3+}\text{:}^3F_4 \rightarrow ^3H_6$ emission can be divided into two parts

upon 3H_4 excitation. One is contributed by the intrinsic relaxation of $^3H_4 \rightarrow ^3F_4$ responsible for Tm^{3+} singly doped sample (under the black line), denoted as I_0 . The other is contributed by FBET responsible for the emission enhancement due to the effect of the codopant Yb^{3+} (shaded area), denoted as ΔI . The portion of 3H_4 population to populate the 3F_4 level via FBET process is then expressed as $\eta_{Tm-Yb} \eta_{Yb-Tm}$ and the 3H_4 population without undergoing FET is $1 - \eta_{Tm-Yb}$ of which $\theta(1 - \eta_{Tm-Yb})$ populates the 3F_4 level through intrinsic relaxation. Therefore, we have

$$\frac{\Delta I}{I_0} = \frac{\eta_{Tm-Yb} \eta_{Yb-Tm}}{\theta(1 - \eta_{Tm-Yb})} \quad (2)$$

where $\Delta I/I_0$ can be obtained directly from the integral area under the emission spectra in Fig. 2b, θ is calculated to be 0.31 for Y_2O_3 (the calculation details are provided in Supporting Information). Using Eq. (2), η_{Yb-Tm} in Y_2O_3 is calculated and listed in Table 1. One can find η_{Yb-Tm} can reach 88% in Y_2O_3 when codoped with 10 mol% Yb^{3+} although the concentration of Tm^{3+} is as low as 0.05%. Accordingly, such highly efficient BET process makes the efficiency of FBET reach up to 77% in Y_2O_3 for codoping with 10 mol% Yb^{3+} . With regard to the efficient BET from Yb^{3+} to Tm^{3+} , it is suggested that Tm^{3+} prefers transferring energy to a nearby Yb^{3+} in the forward process of FBET, thereby leading to the energy transfer from such excited Yb^{3+} back to Tm^{3+} efficiently, whereas the direct excitation of Yb^{3+} at 980 nm gives equal probability to all Yb^{3+} ions of which only a small fraction has a nearby Tm^{3+} for a low concentration of Tm^{3+} in this work.

To prove the above point, we further compared the intensity of $Tm^{3+}\text{:}^3F_4 \rightarrow ^3H_6$ emission contributed by BET from Yb^{3+} to Tm^{3+} in FBET upon $Tm^{3+}\text{:}^3H_4$ excitation at 782 nm with that upon $Yb^{3+}\text{:}^2F_{5/2}$ direct excitation at 980 nm. Fig. 5 shows the emission spectra of $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) upon 980 nm excitation (solid). The spectra of Yb^{3+} emission as well as the incremental of $Tm^{3+}\text{:}^3F_4 \rightarrow ^3H_6$ emission due to the effect of FBET process upon 782 nm excitation obtained by spectral subtraction from Fig. 2b are also presented (dotted) for comparison, in which, for clarity, the intensity of the Yb^{3+} emission upon 980 nm excitation is scaled to that upon 782 nm excitation. Upon 980 nm excitation, all the Yb^{3+} ions are equally excited, and then, the energy transfer from Yb^{3+} to Tm^{3+} is a random process dominated by energy diffusion. One can readily find that the $Tm^{3+}\text{:}^3F_4 \rightarrow ^3H_6$ emission for 980 nm excitation is always weaker than that upon 782 nm excitation, especially for low doping level of Yb^{3+} . In both cases, since the $Tm^{3+}\text{:}^3F_4 \rightarrow ^3H_6$ emission is entirely due to the energy transfer from Yb^{3+} to Tm^{3+} , the weaker $^3F_4 \rightarrow ^3H_6$ emission for 980 nm

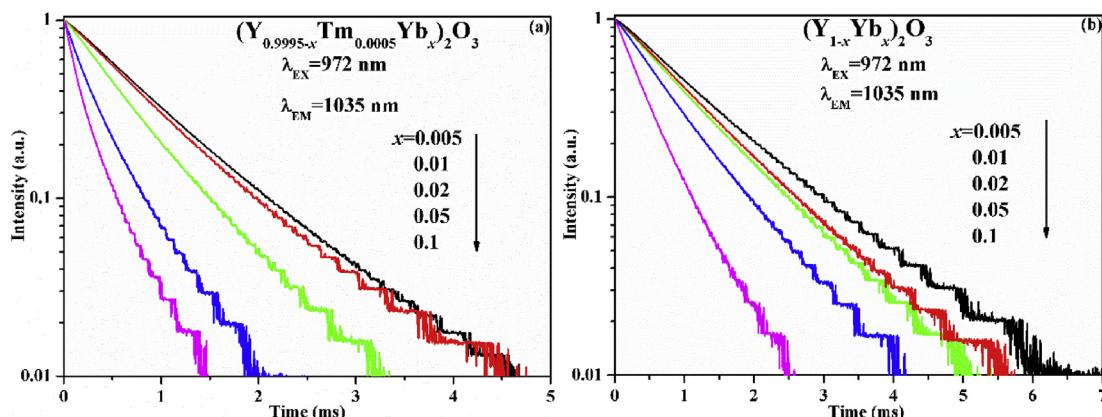


Fig. 6. Fluorescent decay curves of $Yb^{3+}\text{:}^2F_{5/2}$ level in $(Y_{0.9995-x}Tm_{0.0005}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) (a) and in $(Y_{1-x}Yb_x)_2O_3$ ($x = 0.005\text{--}0.1$) upon excitation at 972 nm.

Table 2

The lifetimes of $\text{Yb}^{3+}:\text{F}_{5/2}$ level, the ratio n , BET efficiency $\eta_{\text{Yb-Tm}}$ and the normal energy transfer efficiency $\eta'_{\text{Yb-Tm}}$ in $(\text{Y}_{0.9995-x}\text{Tm}_{0.0005}\text{Yb}_x)_2\text{O}_3$ ($x = 0.005\text{--}0.1$).

x	$\tau_0(\mu\text{s})$	$\tau(\mu\text{s})$	$\eta'_{\text{Yb-Tm}}$	n	$\eta_{\text{Yb-Tm}}$
	$\lambda_{\text{EX}} = 972 \text{ nm}$	$\lambda_{\text{EX}} = 972 \text{ nm}$			
	$\lambda_{\text{EM}} = 1033 \text{ nm}$	$\lambda_{\text{EM}} = 1033 \text{ nm}$			
0.005	1240	886	0.29	13.9	0.85
0.01	1100	747	0.23	5.5	0.62
0.02	1030	616	0.40	3.0	0.67
0.05	810	308	0.62	2.4	0.80
0.1	440	188	0.57	2.9	0.80

excitation means lower transfer efficiency. If the intensity ratio of the $\text{Tm}^{3+}:\text{F}_4 \rightarrow \text{H}_6$ emission upon 782 nm excitation (dotted) to that upon 980 nm excitation (solid) is denoted by n , and the efficiency of energy transfer from Yb^{3+} to Tm^{3+} for 980 nm excitation is denoted by $\eta'_{\text{Yb-Tm}}$, then we have

$$n = \frac{\eta_{\text{Yb-Tm}}/(1 - \eta_{\text{Yb-Tm}})}{\eta'_{\text{Yb-Tm}}/(1 - \eta'_{\text{Yb-Tm}})} \quad (3)$$

where $\eta'_{\text{Yb-Tm}}$ can be calculated using Eq. (1) with the fluorescence lifetimes τ_0 and τ of Yb^{3+} in the absence and in the presence of Tm^{3+} , respectively. To obtain the lifetimes of Yb^{3+} , the fluorescence decay curves of $\text{Yb}^{3+}:\text{F}_{5/2}$ level in Yb^{3+} singly doped and codoped samples are upon 980 nm excitation, as shown in Fig. 6(a) and (b). The obtained fluorescence lifetimes of Yb^{3+} , $\eta'_{\text{Yb-Tm}}$ and $\eta_{\text{Yb-Tm}}$ calculated by Eq. (3) are listed in Table 2. Comparing Table 2 with Table 1, one can conclude that the values of $\eta_{\text{Yb-Tm}}$ calculated by Eq. (2) and that by Eq. (3) are consistent with each other. One may notice from Fig. 5 and Table 2 that the n value decreases from 13.9 to 2.9 with Yb^{3+} concentration increasing from $x = 0$ to $x = 0.1$. The above decrease indicates that the energy diffusion among Yb^{3+} with the increase of Yb^{3+} concentration is unavoidable and it weakens the selectivity between Yb^{3+} and Tm^{3+} in the backward energy transfer process. The increased energy diffusion goes against the effect of preferential excitation of Yb^{3+} that followed by transferring to a nearby Tm^{3+} . Therefore, the backward energy transfer process is more effective in the lowly doping samples.

4. Conclusions

In summary, the emission intensity of $\text{Tm}^{3+}:\text{F}_4 \rightarrow \text{H}_6$ transition is enhanced by 1.8 times through introducing Yb^{3+} into Tm^{3+} -doped Y_2O_3 upon 782 nm excitation, in which the population of F_4 level is increased by backward energy transfer from Yb^{3+} following the forward energy transfer from the upper level $\text{Tm}^{3+}:\text{H}_4$ to an intermediate level $\text{Yb}^{3+}:\text{F}_{5/2}$. The FBET process in $(\text{Y}_{0.9995-x}\text{Tm}_{0.0005}\text{Yb}_x)_2\text{O}_3$ is investigated in detail as a function of Yb^{3+} concentration. The BET efficiency is calculated to be as high as 88% for codoping with 10 mol% Yb^{3+} . The FBET process is also compared with the normal energy transfer process upon direct excitation to Yb^{3+} at 980 nm, indicating that the BET is usually more efficient than the normal energy transfer, especially when the Yb^{3+} concentration is relatively low, which is explained by the preferential excitation of Yb^{3+} with a nearby Tm^{3+} in the FET process. Our results demonstrate that Yb^{3+} can act as an effective bridge between the upper and excitation level H_4 and the lower and emitting level F_4 of Tm^{3+} to obtain efficient 2 μm emission. Furthermore, the efficient backward energy transfer that is in favor of the population of the lower energy level may also play a key role in other codoped luminescence materials.

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Appendix A. Supplementary data

Supplementary data related to this article can be found at <http://dx.doi.org/10.1016/j.jallcom.2017.06.088>.

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